

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,833,308 B2
DATED : December 21, 2004
INVENTOR(S) : Ahn et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], **References Cited**, OTHER PUBLICATIONS, "Guo, X., et al." reference, delete "TiO₂/Si₃N₄" and insert -- TiO₂/Si₃N₄ --, therefor.
"Togo, M., et al." reference, delete "DRAMs" and insert -- DRAMs --, therefor.

Column 1,

Line 8, delete "6,297,103" and insert -- 6,217,103 --, therefor.

Column 10,

Line 13, after "exhibits" delete "a".
Lines 20, 24 and 56, delete "(SiO₂)" and insert -- (SiO₂) --, therefor.
Lines 25, 37 and 57, delete "(Si₃N₄)" and insert -- (Si₃N₄) --, therefor.

Column 11,

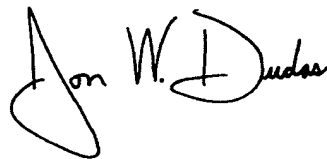
Lines 7, 31, 39 and 61, delete "(Si₃N₄)" and insert -- (Si₃N₄) --, therefor.
Lines 13, 30, 34, 60 and 64, delete "(SiO₂)" and insert -- (SiO₂) --, therefor.
Line 18, delete ":" and insert -- ; --, therefor.
Line 42, after "exhibits" insert -- higher --.

Column 12,

Lines 7, 23 (both occurrences) and 34, delete "(Si₃N₄)" and insert -- (Si₃N₄) --, therefor.
Lines 18 and 49, delete "(SiO₂)" and insert -- (SiO₂) --, therefor.
Line 31, after "including" delete "," and insert -- : --, therefore.
Line 43, after "thickness" insert -- of --.

Signed and Sealed this

Thirty-first Day of May, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office